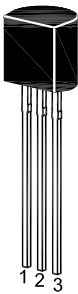


2N6520

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

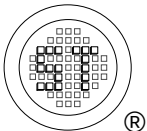
On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	350	V
Collector Emitter Voltage	-V _{CEO}	350	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	500	mA
Power Dissipation	P _{tot}	625	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C



Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{CE} = 10\text{ V}$, $-I_C = 1\text{ mA}$	h_{FE}	20	-	-
at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$	h_{FE}	30	-	-
at $-V_{CE} = 10\text{ V}$, $-I_C = 30\text{ mA}$	h_{FE}	30	200	-
at $-V_{CE} = 10\text{ V}$, $-I_C = 50\text{ mA}$	h_{FE}	20	200	-
at $-V_{CE} = 10\text{ V}$, $-I_C = 100\text{ mA}$	h_{FE}	15	-	-
Collector Base Cutoff Current at $-V_{CB} = 250\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	350	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	350	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage				
at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V
at $-I_C = 20\text{ mA}$, $-I_B = 2\text{ mA}$	$-V_{CE(sat)}$	-	0.35	V
at $-I_C = 30\text{ mA}$, $-I_B = 3\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage				
at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$	$-V_{BE(sat)}$	-	0.75	V
at $-I_C = 20\text{ mA}$, $-I_B = 2\text{ mA}$	$-V_{BE(sat)}$	-	0.85	V
at $-I_C = 30\text{ mA}$, $-I_B = 3\text{ mA}$	$-V_{BE(sat)}$	-	0.9	V
Base Emitter On Voltage at $-V_{CE} = 10\text{ V}$, $-I_C = 100\text{ mA}$	$-V_{BE(on)}$	-	2	V
Gain Bandwidth Product at $-V_{CE} = 20\text{ V}$, $-I_C = 10\text{ mA}$, $f = 20\text{ MHz}$	f_T	40	200	MHz
Collector Base Capacitance at $-V_{CB} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	6	pF

